

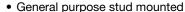
Phase Control Thyristor RMS SCRs, 25 A, 35 A

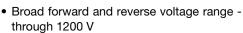


TO-48 (TO-208AA)

PRIMARY CHARACTERISTICS					
I _{T(AV)}	16 A, 22 A				
I _{T(RMS)}	25 A, 35 A				
V _{DRM} /V _{RRM} 25 V, 50 V, 100 V, 150 V, 200 V, 250 300 V, 400 V, 500 V, 600 V, 700 V, 800 1000 V 1200 V					
V _{TM}	2.3 V				
I _{GT}	60 mA				
T_J	-40 °C to +125 °C				
Package	TO-48 (TO-208AA)				
Circuit configuration Single SCR					

FEATURES







 Material categorization: for definitions of compliance please see www.vishav.com/doc?99912

WAJUK KATIN	GS AND CHARACTERIST	103			
PARAMETER	TEST CONDITIONS	VALUES 2N681-92	VALUES 2N5205-07	UNITS	
		16 ⁽¹⁾	22 (1)	Α	
I _{T(AV)}	T _C	-65 to +65 ⁽¹⁾	-40 to +40	°C	
I _{T(RMS)}		25	35	Α	
1	50 Hz	145	285	^	
I _{TSM}	60 Hz	150 ⁽¹⁾	300 (1)	Α	
121	50 Hz	103	410	- A ² s	
I ² t	60 Hz	94	375		
I _{GT}		40	40	mA	
dV/dt		-	100 (1)	V/µs	
dl/dt		75 to 100	100	A/µs	
V_{DRM}	Range	25 to 800	600 to 1200	V	
V _{RRM}	Range	25 to 800	600 to 1200	V	
TJ		-65 to +125 ⁽¹⁾	-40 to +125 ⁽¹⁾	°C	

Note

(1) JEDEC® registered value



ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS (APPLIED GATE VOLTAGE ZERO OR NEGATIVE)						
TYPE NUMBER	V _{RRM} /V _{DRM} , MAXIMUM REPETITIVE PEAK REVERSE AND OFF-STATE VOLTAGE V	V_{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE ($t_p < 5 \text{ ms}$)	TJ			
VS-2N681	25	35				
VS-2N682	50	75				
VS-2N683	100	150				
VS-2N684	150	200				
VS-2N685	200	300				
VS-2N686	250	350	05 00 + 105 00			
VS-2N687	300	400	-65 °C to +125 °C			
VS-2N688	400	500				
VS-2N689	500	600				
VS-2N690	600	720				
VS-2N691	700	840				
VS-2N692	800	960				
VS-2N5205	800	960				
VS-2N5206	1000	1200	-40 °C to +125 °C			
VS-2N5207	1200	1440				

Note

• JEDEC registered values

ABSOLUTE MAXIMUM RATINGS								
PARAMETER	SYMBOL	TEST CON	VALUES 2N681-92	VALUES 2N5205-07	UNITS			
Maximum average on-state	I . (A) 0	180° half sine wave condu	ction	16 ⁽¹⁾	22 ⁽¹⁾	Α		
current at case temperature	I _{T(AV)}	100 Hall Sille wave collud	Clion	-65 to +65 ⁽¹⁾	-40 to +40 ⁽¹⁾	°C		
Maximum RMS on-state current	I _{T(RMS)}			25	35	Α		
		50 Hz half cycle sine wave or 6 ms rectangular pulse	Following any rated load condition, and	145	285	Α		
Maximum peak, one-cycle	I _{TSM}	60 Hz half cycle sine wave or 5 ms rectangular pulse	with rated V _{RRM} applied following surge	150 ⁽¹⁾	300 (1)			
non-repetitive surge current		50 Hz half cycle sine wave or 6 ms rectangular pulse	Same conditions as above except with V _{RRM} applied following surge = 0	170	340			
		60 Hz half cycle sine wave or 5 ms rectangular pulse		180	355			
		t = 10 ms	Rated V _{RRM} applied	103	410			
Maximum I ² t capability for fusing	I ² t	t = 8.3 ms	following surge, initial T _J = 125 °C	94	375	A ² s		
Maximum I2t capability for		t = 10 ms	V _{RRM} = 0 following	145	580			
individual device fusing		t = 8.3 ms	surge, initial T _J = 125 °C	135	530			
Maximum l²√t capability for individual device fusing	I ² √t ⁽²⁾	$t = 0.1$ ms to 10 ms, initial V_{RRM} applied following sur	1450	5800	A²√s			
Maximum peak on-state voltage	V _{TM}	$T_J = 25$ °C, $I_{T(AV)} = 16$ A (50 $I_{T(AV)} = 22$ A (70 A peak) 2N	2 (1)	2.3 (1)	V			
Maximum holding current	I _H	Anode supply 24 V, initial I	20 at 25 °C (typical)	200 ⁽¹⁾ at -40 °C	mA			

Notes

⁽¹⁾ JEDEC registered value

⁽²⁾ I^2t for time $t_x = I^2 \sqrt{t} \cdot \sqrt{t_x}$



SWITCHING							
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES 2N681-92	VALUES 2N5205-07	UNITS	
	V _{DM} = 25 V to 600 V		$T_C = 125 ^{\circ}\text{C}, V_{DM} = \text{Rated } V_{DRM},$	100	-		
Maximum non-repetitive rate of rise of turned-on current	V _{DM} = 700 V to 800 V	- dl/dt -	I_{TM} = 2 x dI/dt, gate pulse = 20 V, 15 Ω , t_p = 6 μ s, t_r = 0.1 μ s maximum Per JEDEC standard RS-397, 5.2.2.6	75	-	A/us	
			T_C = 125 °C, V_{DM} = 600 V, I_{TM} = 200 A at 400 Hz maximum, gate pulse = 20 V, 15 Ω , t_p = 6 μ s, t_r = 0.1 μ s maximum Per JEDEC standard RS-397, 5.2.2.6	-	100	Ανμδ	
Typical delay time		t _d	T_C = 25 °C, V_{DM} = Rated V_{DRM} , I_{TM} = 10 A DC resistive circuit, gate pulse = 10 V, 40 Ω source, t_p = 6 μ s, t_r = 0.1 μ s	1	1	μs	

BLOCKING							
PARAMETER		SYMBOL	TEST CONDITIONS		VALUES 2N681-92	VALUES 2N5205-07	UNITS
Minimum critical rate of rise of off-state voltage		dV/dt	$T_J = 125$ °C, exponential to 100 % rated V_{DRM}	Gate open circuited	100 (typical)	100 (1)	V/µs
			$T_J = 125$ °C, exponential to 67 % rated V_{DRM}		250 (typical)	250	
	V_{RRM} , $V_{DRM} = 400 \text{ V}$				3.5	-	
	V_{RRM} , $V_{DRM} = 500 V$			3.5	-		
Marrianous	V_{RRM} , $V_{DRM} = 600 V$] ,	T _J = 125 °C		2.5	3.3	
Maximum reverse leakage current	V_{RRM} , $V_{DRM} = 700 V$	I _{DRM} ,			2.2	-	mA
	V_{RRM} , $V_{DRM} = 800 V$	IRRM			2	2.5	
	V _{RRM} , V _{DRM} = 1000 V				-	2	
	V _{RRM} , V _{DRM} = 1200 V	1			-	1.7	

Note

(1) JEDEC registered value

TRIGGERING						
PARAMETER	SYMBOL		TEST CONDITIONS		VALUES 2N5205-07	UNITS
Maximum peak gate power	P _{GM}	t _p < 5 ms for 2N681 series; t _o < 500 μs for 2N5204 series		5 (1)	60 ⁽¹⁾	W
Maximum average gate power	P _{G(AV)}			0.5 (1)	0.5 (1)	
Maximum peak positive gate current	+I _{GM}			2 (1)	2	Α
Maximum peak positive gate voltage	+V _{GM}			10 ⁽¹⁾	-	V
Maximum peak negative gate voltage	-V _{GM}			5 ⁽¹⁾	5 ⁽¹⁾	V
Maximum required DC gate current to trigger	I _{GT}	T _C = min. rated value	Maximum required gate trigger current is the lowest value which will trigger all units with + 6 V anode to cathode	80 (1)	80 (1)	
		T _C = 25 °C		40	40	mA
		T _C = 125 °C		18.5	20	
Typical DC gate current to trigger		$T_C = 25 ^{\circ}C, +$	6 V anode to cathode	30	30	
Maximum required DC gate voltage to trigger	V _{GT}	T _C = -65 °C	Maximum required gate trigger voltage is the lowest value which will trigger all units with + 6 V anode to cathode	3 (1)	3 (1)	V
		T _C = 25 °C		2	2	
Typical DC gate voltage to trigger		T _C = 25 °C, + 6 V anode to cathode		1.5	1.5	
Maximum DC gate voltage not to trigger	V_{GD}	T _C = 125 °C	Maximum gate voltage not to trigger is the maximum value which will not trigger any unit with rated V _{DRM} anode to cathode	0.25 (1)	0.25 (1)	V

Note

(1) JEDEC registered value



THERMAL AND MECHANICAL SPECIFICATIONS								
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES 2N681-92	VALUES 2N5205-07	UNITS		
Operating junction and storage temperature range		T _J , T _{Stg}		-65 to 125 ⁽¹⁾	-40 to 125 ⁽¹⁾	°C		
Maximum internal thermal resistance, junction to case		R _{thJC}	DC operation	1.5	1.5 ⁽¹⁾	°C/W		
Typical thermal resistance, case to sink		R _{thCS}	Mounting surface, smooth, flat and greased	0.35	0.35	-0/00		
			Lukii atad thusada	20 (27.5)		lbf · in		
	to nut		Lubricated threads (Non-lubricated threads)	0.23 (0.32)		kgf · cm		
Mounting torque		(NON-Tublicated tilleads)		2.3 (3.1)		N·m		
± 10 %	± 10 % to device		Lubricated threads		25			
					0.29			
					2.8			
Approximate weight	Approximate weight			14	14	g		
Approximate weight				0.49	0.5	OZ.		
Case style				TO-48 (TO-208AA)		·		

Note

⁽¹⁾ JEDEC registered value

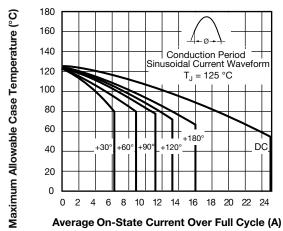


Fig. 1 - Maximum Allowable Case Temperature vs. Average On-State Current, 2N681 Series

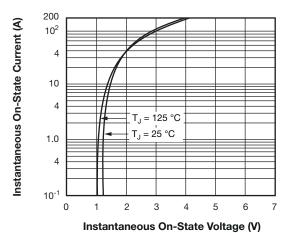
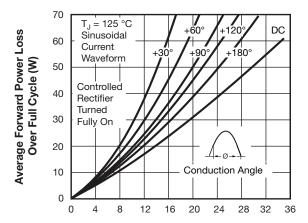


Fig. 2 - Maximum On-State Voltage vs. Current, 2N681 Series



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Average On-State Current Over Full Cycle (A)

Fig. 3 - Maximum Low Level On-State Power Loss vs. Current (Sinusoidal Current Waveform), 2N681 Series

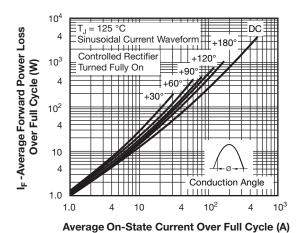
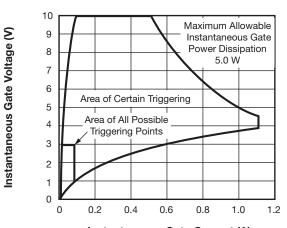


Fig. 4 - Maximum High Level On-State Power Loss vs. Current (Sinusoidal Current Waveform), 2N681 Series



Instantaneous Gate Current (A)
Fig. 5 - Gate Characteristics,
2N681 Series

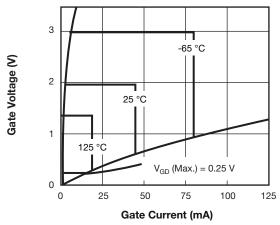


Fig. 5a - Area of All Possible Triggering Points vs. Temperature, 2N681 Series

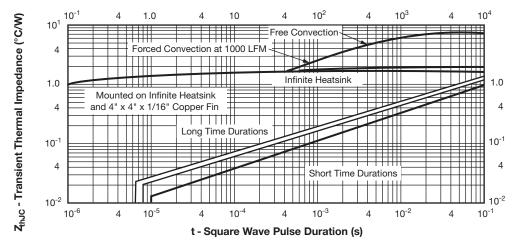


Fig. 6 - Maximum Transient Thermal Impedance, Junction to Case, vs. Pulse Duration, 2N681 Series

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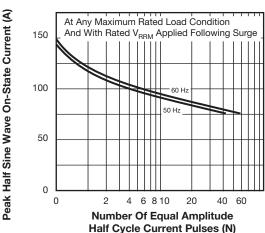


Fig. 7 - Maximum Non-Repetitive Surge Current vs. Number of Current Pulses, 2N681 Series

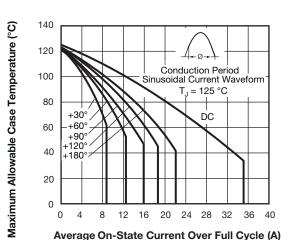


Fig. 8 - Maximum Allowable Case Temperature vs. Average On-State Current (Sinusoidal Current Waveform), 2N5205 Series

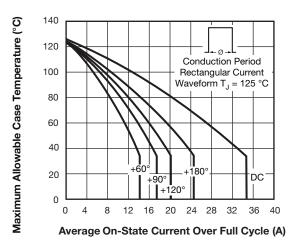
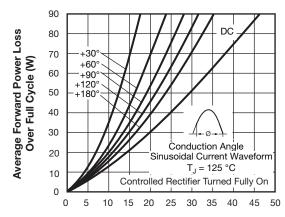


Fig. 9 - Maximum Allowable Case Temperature vs. Average On-State Current (Rectangular Current Waveform), 2N5205 Series



Average On-State Current Over Full Cycle (A)

Fig. 10 - Maximum Low-Level On-State Power Loss vs. Average On-State Current (Sinusoidal Current Waveform), 2N5205 Series

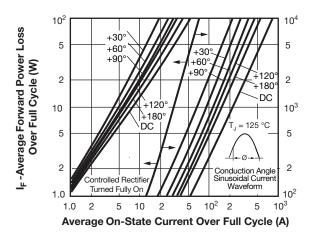
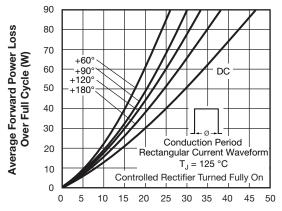


Fig. 11 - Maximum High-Level On-State Power Loss vs. Average On-State Current (Sinusoidal Current Waveform), 2N5205 Series



Average On-State Current Over Full Cycle (A)

Fig. 12 - Maximum Low-Level On-State Power Loss vs. Average On-State Current (Rectangular Current Waveform), 2N5205 Series



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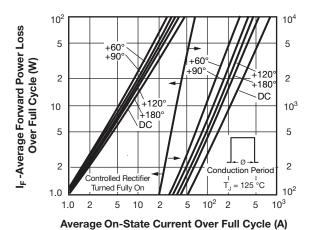


Fig. 13 - Maximum High-Level On-State Power Loss vs. Average On-State Current (Rectangular Current Waveform), 2N5205 Series

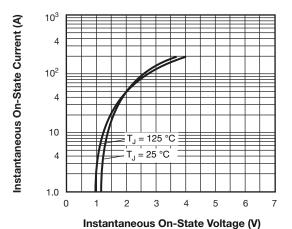


Fig. 14 - Maximum Instantaneous On-State Voltage vs. Instantaneous On-State Current, 2N5205 Series

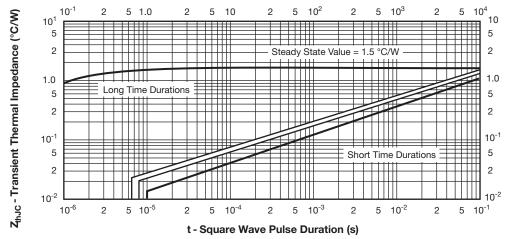


Fig. 15 - Maximum Transient Thermal Resistance, Junction to Case vs. Pulse Duration, 2N5205 Series

LINKS TO RELATED DOCUMENTS					
Dimensions www.vishay.com/doc?95333					



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